# N-Channel 60-V (D-S) MOSFET

## **Key Features:**

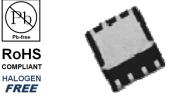
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

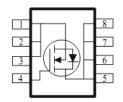
### **Typical Applications:**

- DC/DC Conversion Circuits
- Motor Drives

PRODUCT SUMMARY				
Vds (V)	$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$			
60	50 @ V <sub>GS</sub> = 10V	6.9		
00	60 @ V <sub>GS</sub> = 4.5V	6.3		







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			60	V		
Gate-Source Voltage	V <sub>GS</sub>	±20	V			
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	1	6.9	А		
Continuous Drain Current	T <sub>A</sub> =70°C	I <sub>D</sub>	5.5			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	25				
Continuous Source Current (Diode Conduction) <sup>a</sup>		۱ <sub>s</sub>	4.6	А		
Dower Dissinction <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	3.6	W		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	U 'D	2.3	vv		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	R <sub>eja</sub>	35	°C/W		
	Steady State	νθJA	75			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

# **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
	I <sub>DSS</sub>	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	10			А	
Drain Course On Desistance a	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 5.4 \text{ A}$			50	mO	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 4.4 \text{ A}$			60	mΩ	
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 5.4 \text{ A}$		9		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.79		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_{g}$	$V_{DS} = 30 \text{ V}, V_{GS} = 4.5 \text{ V},$		3.8			
Gate-Source Charge	$Q_gs$	$v_{\rm DS} = 50  \text{v},  v_{\rm GS} = 4.5  \text{v},  I_{\rm D} = 5.4  \text{A}$		1.3		nC	
Gate-Drain Charge	$Q_gd$	1 <u>0</u> – 0.4 A		1.2			
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = 30 V, R <sub>I</sub> = 5.6 Ω,		3			
Rise Time	t <sub>r</sub>	$V_{\rm DS} = 30$ V, $N_{\rm L} = 3.0$ 22, $I_{\rm D} = 5.4$ A,		5		nc	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		19		ns	
Fall Time	t <sub>f</sub>	VGEN - 10 V, TCGEN - 0 22		6			
Input Capacitance	C <sub>iss</sub>			346			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1 Mhz		52		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			30			

#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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1.2

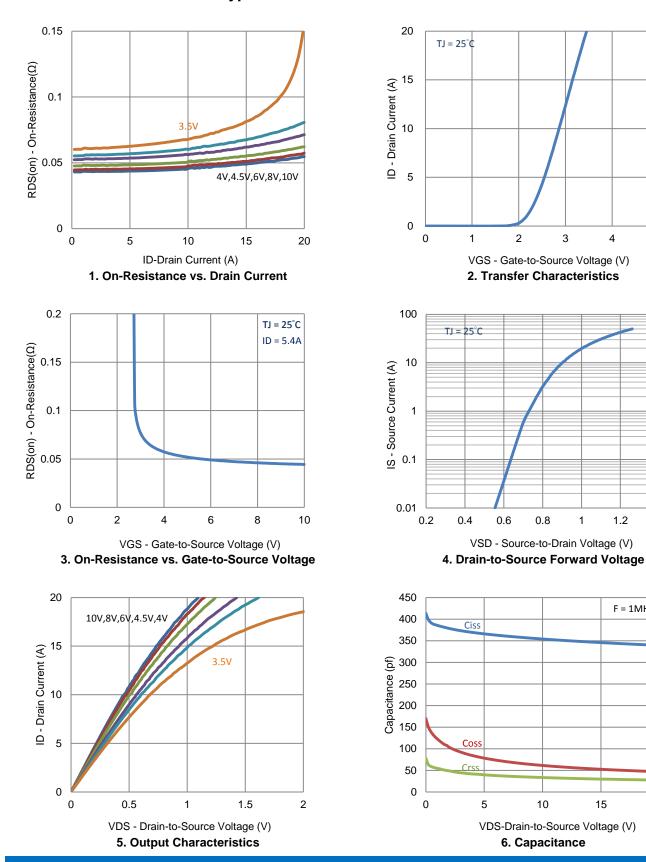
F = 1MHz

1.4

20

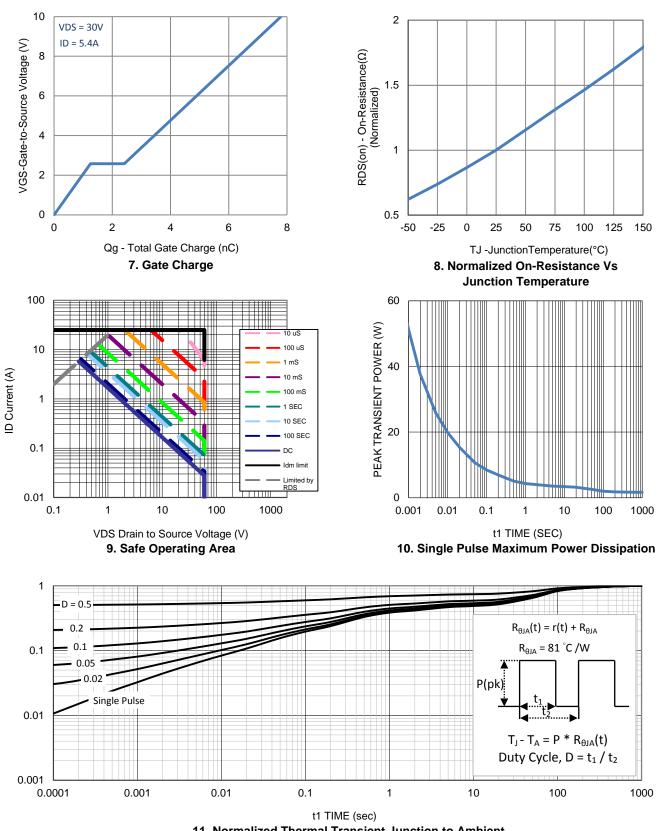
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## **Typical Electrical Characteristics**

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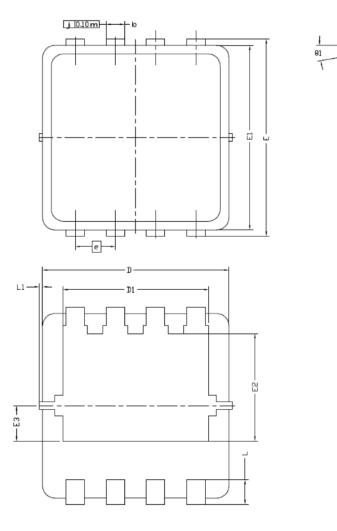


### **Typical Electrical Characteristics**

**11. Normalized Thermal Transient Junction to Ambient** 

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# Package Information



птм	MILLIMETERS			INCHES			
DIM,	MIN NOM		MAX	MIN	NDM	MAX	
Α	0,700	0,80	0,900	0,0276	0,0315	0,0354	
A1	0,00		0,05	0.000		0'005	
b	0.24	0.30	0.35	0.009	0.012	0.014	
С	0,10	0.152	0.25	0.004	0.006	0.010	
D	3,00 BSC			0.118 BSC			
D1	2.35 BSC			0.093 BSC			
E	3.20 BSC			0.126 BSC			
E1	3.00 BSC			0.118 BSC			
E2	1.75 BSC			0.069 BSC			
E3	0.575 BSC			0.023 BSC			
е	0.65 BSC		0.026 BSC				
L	0,30	0,40	0,50	0,0118	0,0157	0,0197	
L1	0		0,100	0		0.004	
θ1	0*	10°	12°	0*	10°	12°	